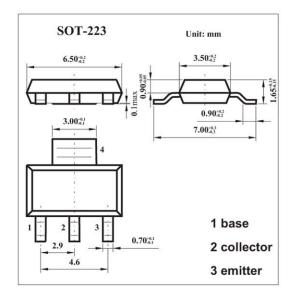


BCP54--BCP56

Features

High collector current

1.3 W power dissipation.



Absolute Maximum Ratings Ta = 25[°]C

Parameter		Symbol	Rating	Unit
collector-base voltage	BCP54		45	V
	BCP55	Vсво	60	٧
	BCP56		100	V
collector-emitter voltage	BCP54		45	V
	BCP55	Vceo	60	٧
	BCP56]	80	V
emitter-base voltage		Vево	5	V
collector current (DC)		Ic	1	Α
peak collector current		Ісм	1.5	А
peak base current		Івм	0.2	Α
total power dissipation		Ptot	1.33	W
storage temperature		Tstg	-65 to +150	°C
junction temperature		Tj	150	°C
operating ambient temperature		Tamb	-65 to +150	°C
thermal resistance from junction to ambient		Rth j-a	94	K/W
thermal resistance from junction to soldering point		Rth j-s	13	K/W



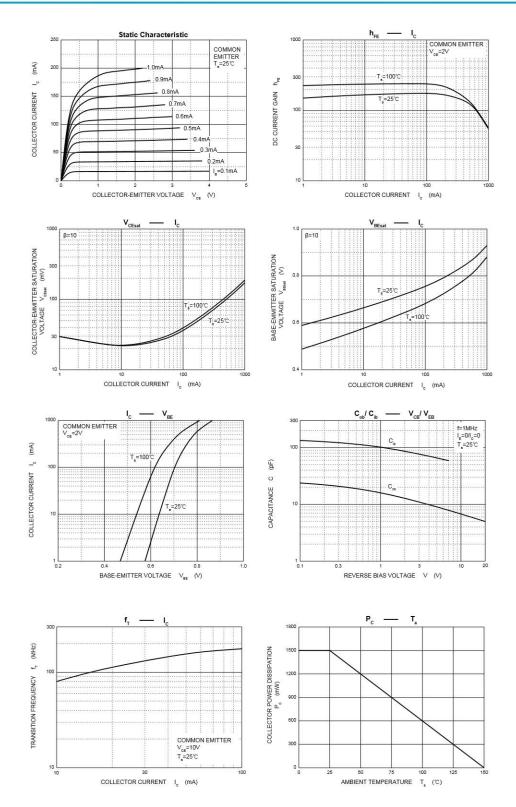
BCP54--BCP56

● Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Тур	Max	Unit
collector cut-off current	Ісво	IE = 0 A; VcB = 30 V			100	nA
collector cut-on current		IE = 0 A; VcB = 30 V; Tj = 150 ℃			10	μA
emitter cut-off current	ІЕВО	Ic = 0 A; VEB = 5 V			100	nA
	hFE	Ic = 5 mA; VcE = 2 V	63			
DC current gain		Ic =150 mA; VcE = 2 V	63		250	
		Ic = 500 mA; VcE = 2 V	40			
DC current gain BCP54;BCP55;BCP56	hFE	VcE = 2 V; Ic = 150 mA	63		250	
BCP54-10; BCP55-10; BCP56-10			63		160	
BCP54-16; BCP55-16; BCP56-16			100		250	
collector-emitter saturation voltage	VCEsat	Ic = 0.5 A; IB = 50 mA			500	mV
base-emitter voltage	VBE	Ic = 0.5 A; VcE = 2 V			1	V
transition frequency	fī	Ic = 10 mA; VcE = 5 V; f = 100 MHz		130		MHz
DC current gain ratio of the complementary pairs	h _{FE1} h _{FE2}	Ic = 150 mA; Vce = 2 V			1.6	



BCP54--BCP56



单击下面可查看定价,库存,交付和生命周期等信息

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